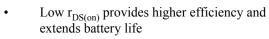
## N-Channel 30V (D-S) MOSFET These miniature surface mount MOSFETs

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r<sub>DS(on)</sub> and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

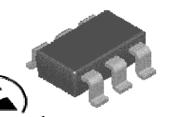
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$V_{DS}(V)$ $r_{DS(on)}(\Omega)$			
30	$0.032@V_{CS}=10V$	5.3		
	$0.044 @V_{CS} = 4.5V$	4.5		

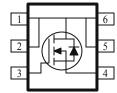


 Low thermal impedance copper leadframe TSOP-6 saves board space

Fast switching speed

High performance trench technology ESD Protected





ESD Protected 2000V

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Maximum	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage			±20	V		
Continuous Durin Communia	$T_A=25^{\circ}C$	J.,	5.5			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	4.4	A		
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	±20			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.3	A		
D Dii4ia	$T_A=25^{\circ}C$	D.,	2.0	W		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	Гр	1.3			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M · I · · · a	t <= 5 sec	$R_{\mathrm{THJA}}$	85	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	КТНЈА	62.5			

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Davamatar	Cymb al	Test Conditions	Limits			TT*4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	- Unit	
Switch Off Characteristics							
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			1 10	uA	
Switch On Characteristics		20 / 00 / 1					
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1.0			V	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 5.3 \text{ A}$			32	mΩ	
Diani-Source On-Resistance	<sup>1</sup> DS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 4.5 \text{ A}$			44	1115.2	
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 10 \text{ V}, I_D = 5.3 \text{ A}$		45		S	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{\mathrm{g}}$	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 5.3 \text{ A}$		4.0			
Gate-Source Charge	$Q_{gs}$	$R_{\rm I} = 6 \Omega$		1.1		nC	
Gate-Drain Charge	$Q_{gd}$	$R_{ m L} = 0.22$		1.4			
Turn-On Delay Time	$t_{d(on)}$			6			
Rise Time	t <sub>r</sub>	$V_{DS} = 15 \text{ V},  R_L = 6 \Omega,  I_D = 1 \text{ A},$		10		nc	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		18		ns	
Fall-Time	$t_{\mathrm{f}}$			5			

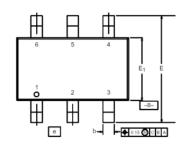
## Notes

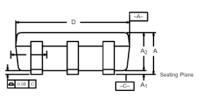
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

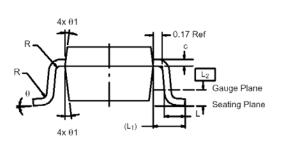
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## Package Information

TSOP-6: 6LEAD







	MILLIMETERS				NCHES	;
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	_	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	_	0.004
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	_	_	0.004	_	_
θ	0°	4°	8°	0°	4°	8°
$\theta_1$		7° Nom		7° Nom		